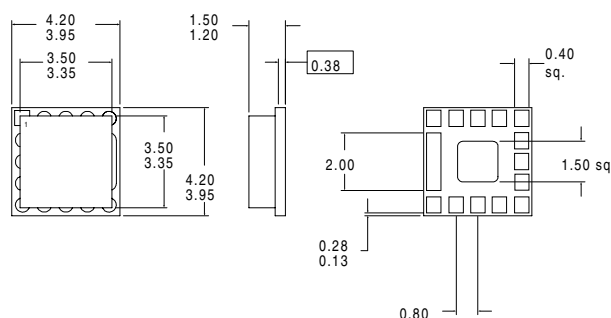


Typical Applications

- PACS Handsets and Base Stations
- 3V 1850-1910MHz CDMA PCS Handsets
- 3V 1750-1780MHz CDMA PCS Handsets
- 3V TDMA PCS Handsets
- Spread Spectrum Systems
- Commercial and Consumer Systems

Product Description

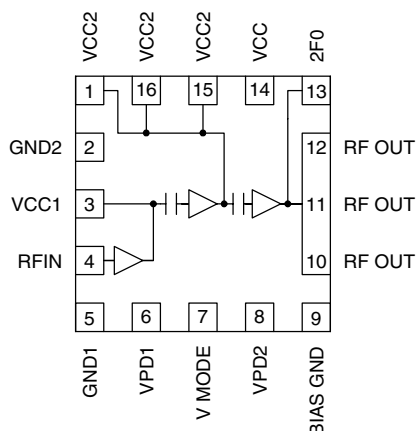
The RF2153 is a high-power, high-efficiency linear amplifier IC targeting 3V handheld systems. The device is manufactured on an advanced Gallium Arsenide Hetero-junction Bipolar Transistor (HBT) process, and has been designed for use as the final RF amplifier in 3V CDMA and TDMA hand-held digital equipment, spread spectrum systems, and other applications in the 1750MHz to 1910MHz band. The device is packaged in a compact 4mmx4mm (LCC). The device's frequency response can be optimized for linear performance in the 1750MHz to 1910MHz band.



ALL SOLDER PAD TOLERANCES P0.05mm

Optimum Technology Matching® Applied

- | | | |
|-------------------------------------|--|--------------------------------------|
| <input type="checkbox"/> Si BJT | <input checked="" type="checkbox"/> GaAs HBT | <input type="checkbox"/> GaAs MESFET |
| <input type="checkbox"/> Si Bi-CMOS | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si CMOS |



Functional Block Diagram

Package Style: MP16KO1A

Features

- Single 3V Supply
- 29dBm Linear Output Power
- 30dB Linear Gain
- 33% Linear Efficiency CDMA
- 40% Linear Efficiency TDMA
- On-board Power Down Mode

Ordering Information

RF2153	CDMA/TDMA/PACS 1900MHz 3V Power Amplifier
RF2153 PCBA	Fully Assembled Evaluation Board

RF Micro Devices, Inc.
7625 Thorndike Road
Greensboro, NC 27409, USA

Tel (336) 664 1233
Fax (336) 664 0454
<http://www.rfmd.com>

Absolute Maximum Ratings

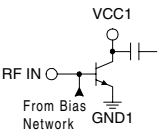
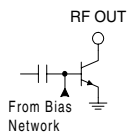
Parameter	Rating	Unit
Supply Voltage (RF off)	+8.0	V _{DC}
Supply Voltage (P _{OUT} ≤31 dBm)	+4.5	V _{DC}
Mode Voltage (V _{MODE})	+3.5	V _{DC}
Control Voltage (V _{PD})	+3.5	V _{DC}
Input RF Power	+10	dBm
Operating Case Temperature	-30 to +85	°C
Storage Temperature	-30 to +150	°C



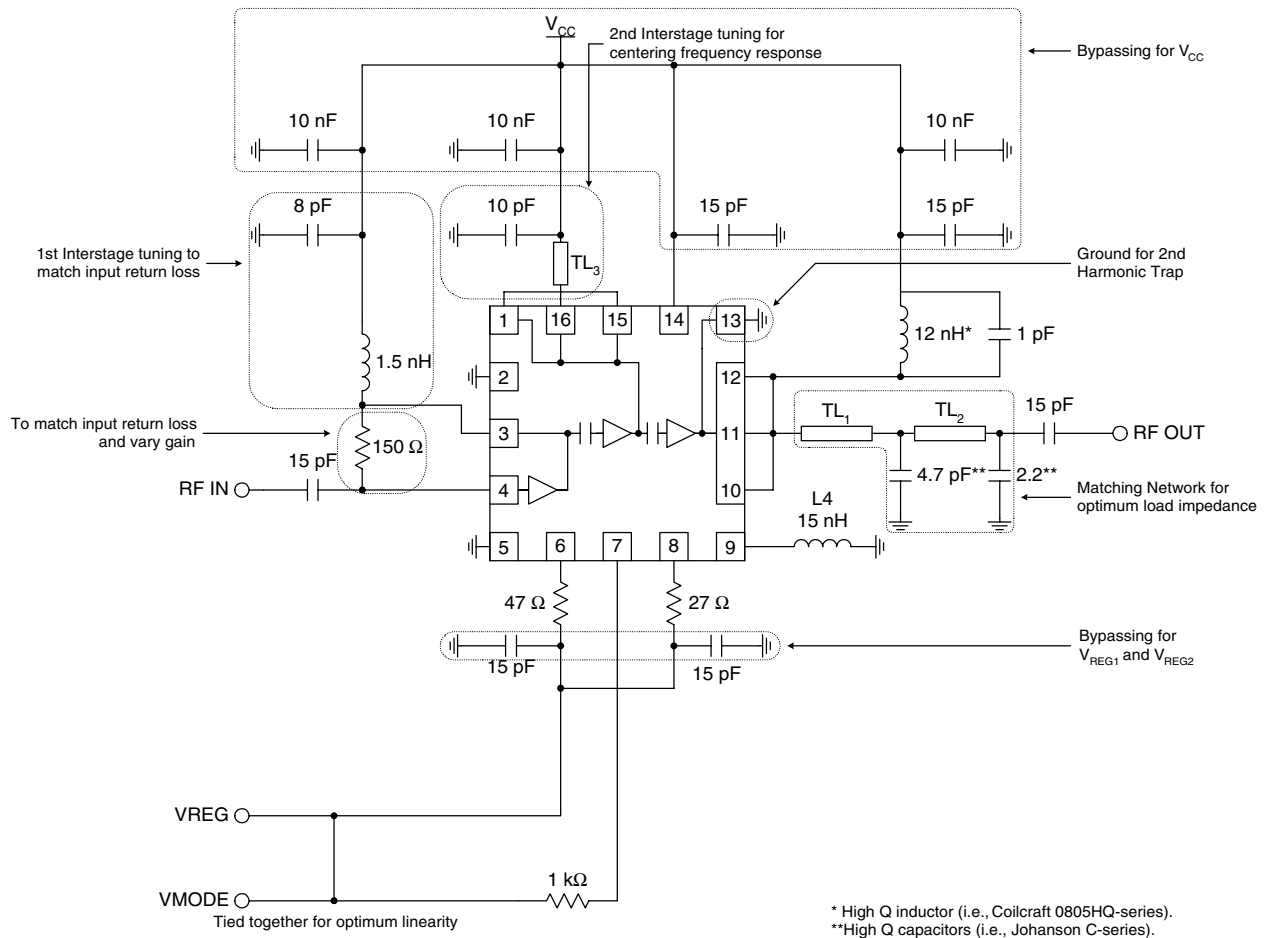
Caution! ESD sensitive device.

RF Micro Devices believes the furnished information is correct and accurate at the time of this printing. However, RF Micro Devices reserves the right to make changes to its products without notice. RF Micro Devices does not assume responsibility for the use of the described product(s).

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Overall - CDMA					T=25°C, V _{CC} =3.4V unless otherwise specified
Usable Frequency Range	1750		1910	MHz	
Typical Frequency Range		1750-1780 1850-1910		MHz	Output Matching Network Tune
Small Signal Gain	30	32	34	dB	V _{MODE} =Low 0V to 0.5V
Linear Gain	28	30		dB	V _{MODE} =High 2.5V to 3V P _{OUT} =29 dBm, V _{CC} =3.4V, V _{REG} =2.8V
Second Harmonic (including second harmonic trap)		-35		dBc	
Third Harmonic		-40		dBc	
Fourth Harmonic		-45		dBc	
Minimum Linear Output Power (CDMA or TDMA Modulation)	29			dBm	
Idle Current		100		mA	V _{MODE} =>2.5V
CDMA Linear Efficiency	30	33			P _{OUT} =29 dBm, V _{CC} =3.4V, V _{REG} =2.8V
CDMA Adjacent Channel Power Rejection @ 1.25MHz		-46	-44	dBc	P _{OUT} =29 dBm, V _{CC} =3.4V, V _{REG} =2.8V
Minimum Linear Output Power (CDMA Modulation)	28	+29		dBm	V _{CC} =3.0V, V _{REG} =2.8V
Input VSWR		< 2:1			
Output Load VSWR	5:1				
Overall - TDMA					T=25°C, V _{CC} =3.4V unless otherwise specified
Idle Current		250	500	mA	V _{MODE} =0V to 0.5V
TDMA Linear Efficiency	30	40		%	P _{OUT} =30 dBm, V _{CC} =3.4V, V _{REG} =2.8V
TDMA ACP @ 30kHz		-29	-28	dBc	P _{OUT} =30 dBm
TDMA ALT @ 60kHz		-49	-48	dBc	P _{OUT} =30 dBm
Power Supply					
Power Supply Voltage	3.0	3.4	4.5	V	
V _{PD} Current		10	15	mA	Total pins 7 and 8
Turn On/Off time			100	ns	
Total Current (Power down)			10	μA	V _{PD} = low
V _{PD} "Low" Voltage		0	0.2	V	
V _{PD} "High" Voltage	2.7	2.8	2.9	V	
MODE "High" Voltage	2.5	2.8		V	
MODE "Low" Voltage		0	0.5	V	
Stability		3:1			Inband
Spurious		20:1			Outband
Noise Power		<-60		dBc	
		-136		dB/Hz	@ 80MHz offset

Pin	Function	Description	Interface Schematic
1	VCC2	Power supply for second stage and interstage match. Pins 1, 15 and 16 should be connected by a common trace where the pins contact the printed circuit board.	
2	GND2	Ground for second stage. Keep traces physically short and connect immediately to ground plane for best performance. This ground should be isolated from the backside ground contact on top metal layer.	
3	VCC1	Power supply for first stage and interstage match. V _{CC} should be fed through a 1.5nH inductor terminated with a 15pF capacitor on the supply side.	See pin 4.
4	RF IN	RF input. An external 15pF series capacitor is required as a DC block and also provides for an input VSWR of <2:1 typical.	
5	GND1	Ground for first stage. Keep traces physically short and connect immediately to ground plane for best performance. This ground should be isolated from the backside ground contact on top metal layer.	See pin 4.
6	VPD1	Power Down control for first and second stages. When this pin is "low", all first and second stage circuits are shut off. When this pin is 2.8V, all first stage circuits are operating normally. V _{PD1} requires a regulated 2.8V for the amplifier to operate properly over all specified temperature and voltage ranges. A dropping resistor from a higher regulated voltage may be used to provide the required 2.8V.	
7	VMODE	For full power operation, MODE is set low. VMODE will reduce the bias current by up to 50% when set HIGH. Large Signal Gain is reduced approximately 1.5dB at 29dBm P _{OUT} and Small Signal Gain is reduced approximately 6dB. An external series resistor is optional to limit the amount of current required by the V _{MODE} pin.	
8	VPD2	Power Down control for the third stage. When this pin is "low", the third stage circuit is shut off. When this pin is 2.8V, the third stage circuit is operating normally. V _{PD} requires a regulated 2.8V for the amplifier to operate properly over all specified temperature and voltage ranges. A dropping resistor from a higher regulated voltage may be used to provide the required 2.8V. A 15pF high frequency bypass capacitor is recommended.	
9	BIAS GND	Requires a 15nH inductor.	
10	RF OUT	RF output and power supply for final stage. This is the unmatched collector output of the third stage. A DC block is required following the matching components. The biasing may be provided via a parallel L-C set for resonance at the operating frequency of 1850MHz to 1910MHz. It is important to select an inductor with very low DC resistance with a 1A current rating. Alternatively, shunt microstrip techniques are also applicable and provide very low DC resistance. Low frequency bypassing is required for stability.	
11	RF OUT	Same as pin 12.	See pin 10.
12	RF OUT	Same as pin 12.	See pin 10.
13	2FO	Second harmonic trap. Keep traces physically short and connect immediately to ground plane. This ground should be isolated from backside ground contact.	
14	VCC	Supply for bias reference and control circuits. High frequency bypassing may be necessary.	
15	VCC2	Same as pin 1.	
16	VCC2	Same as pin 1.	
Pkg Base	GND	Ground connection. The backside of the package should be soldered to a top side ground pad which is connected to the ground plane with multiple vias. The pad should have a short thermal path to the ground plane.	

Application Schematic US - CDMA

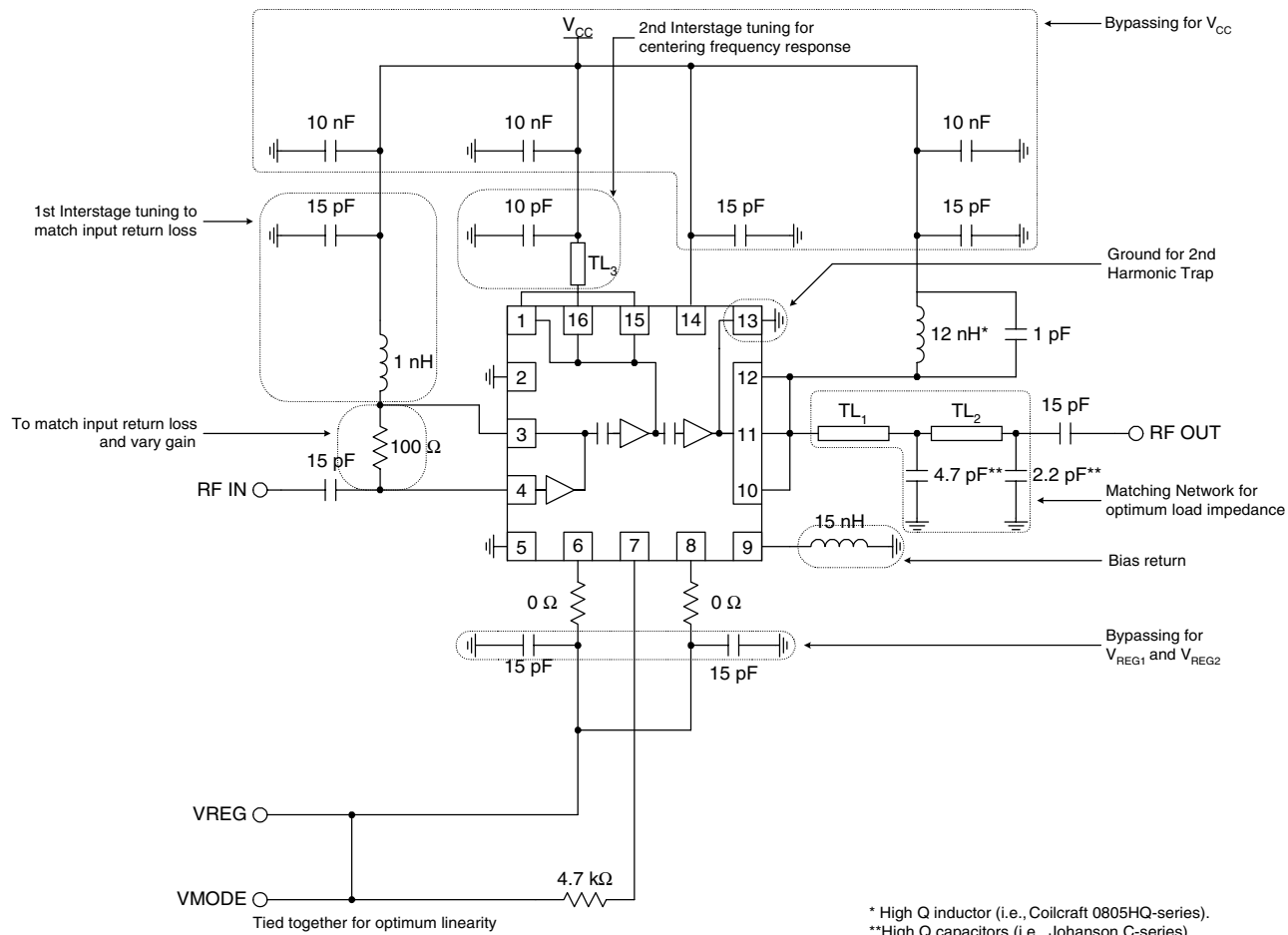


Transmission Line Length	TL ₁	TL ₂	TL ₃
CDMA (US)	20 mils	100 mils	20 mils

Application Schematic US - TDMA

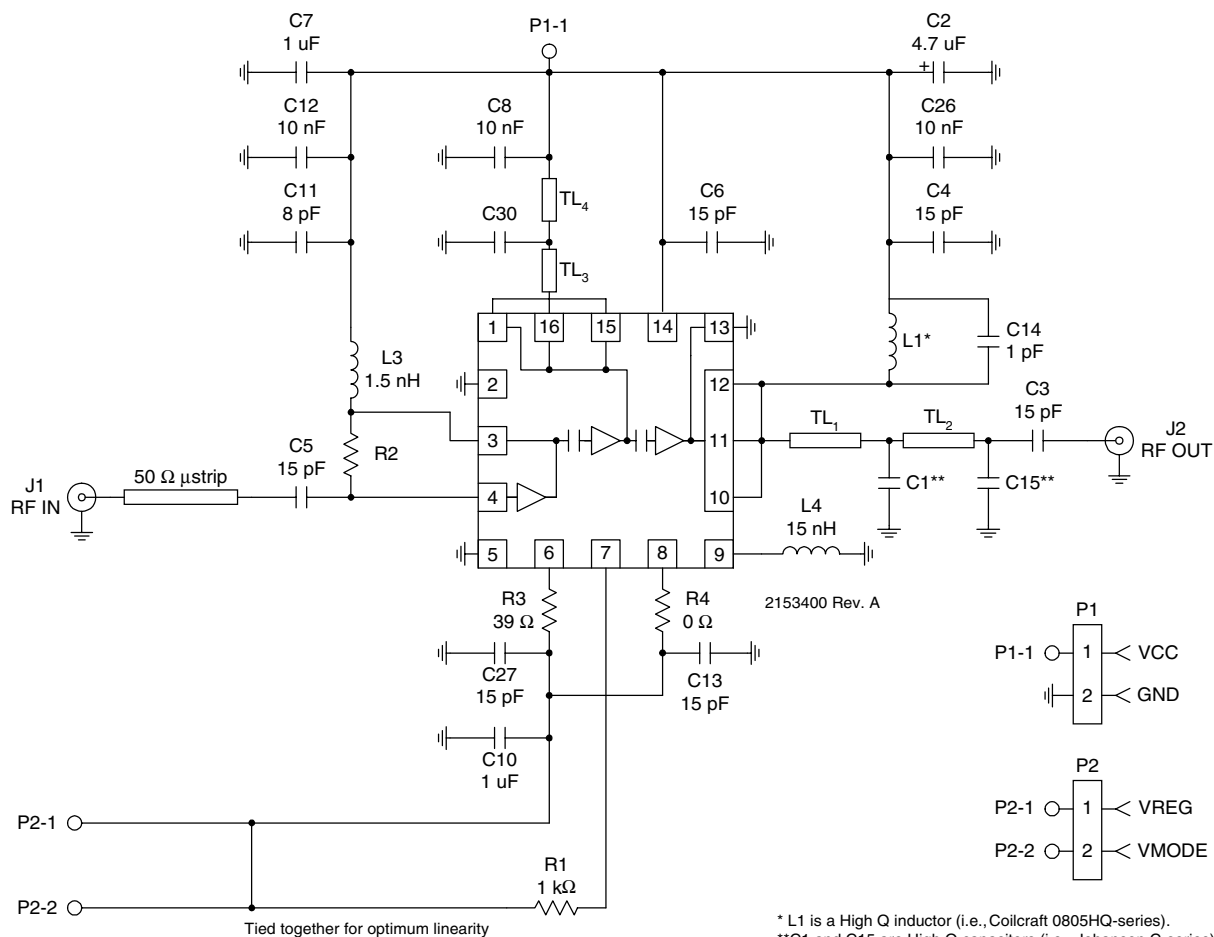
2

POWER AMPLIFIERS



Transmission Line Length	TL ₁	TL ₂	TL ₃
TDMA (US)	20 mils	160 mils	10 mils

Evaluation Board Schematic US - CDMA



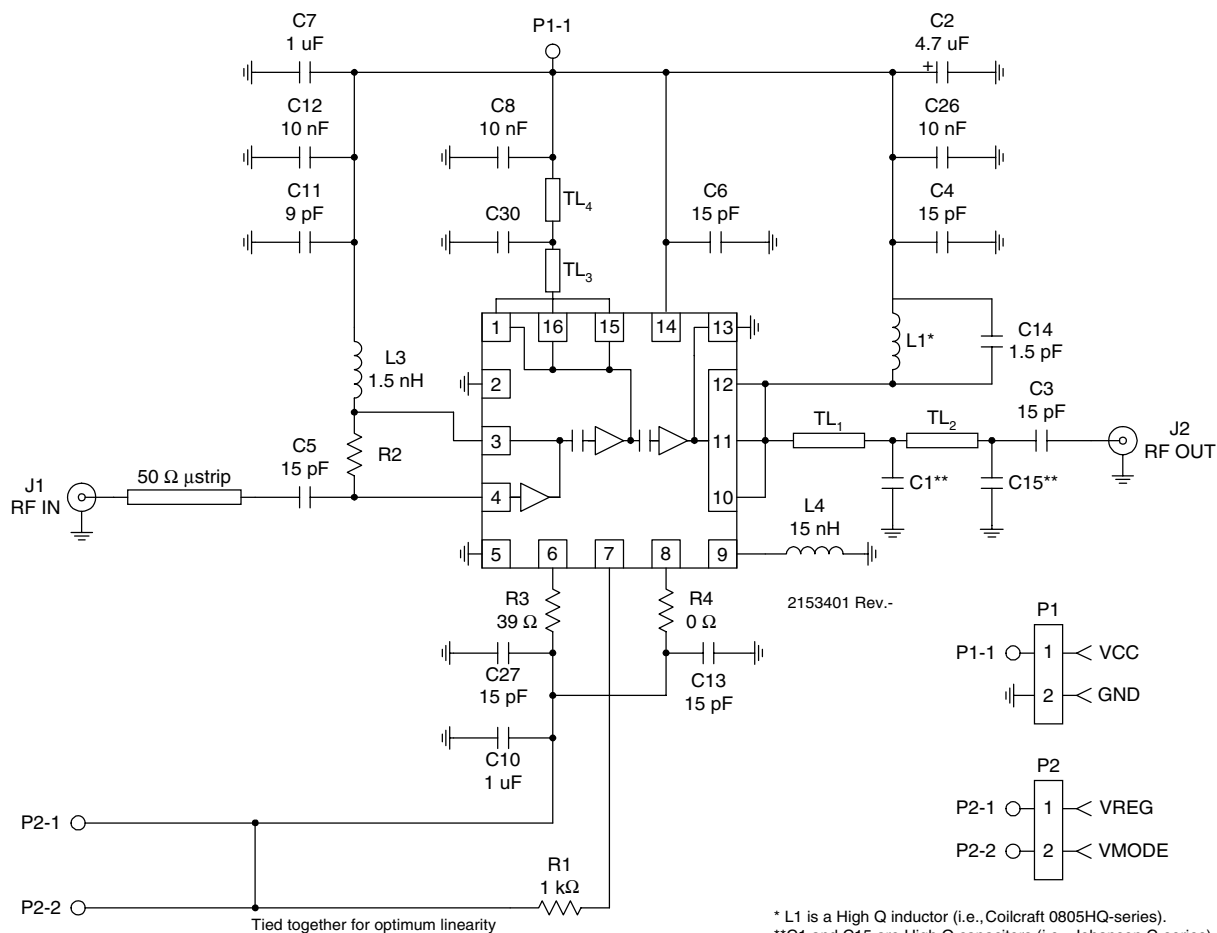
* L1 is a High Q inductor (i.e., Coilcraft 0805HQ-series).

**C1 and C15 are High Q capacitors (i.e., Johanson C-series).

Board	R2 (Ω)	C30 (pF)	C1 (pF)	L1 (nH)	C15 (pF)
CDMA (US)	150	10	4.7	12	2.2

Transmission Line Length	TL ₁	TL ₂	TL ₃	TL ₄
CDMA (US)	20 mils	100 mils	20 mils	100 mils or ≥ 2.7 nH inductor

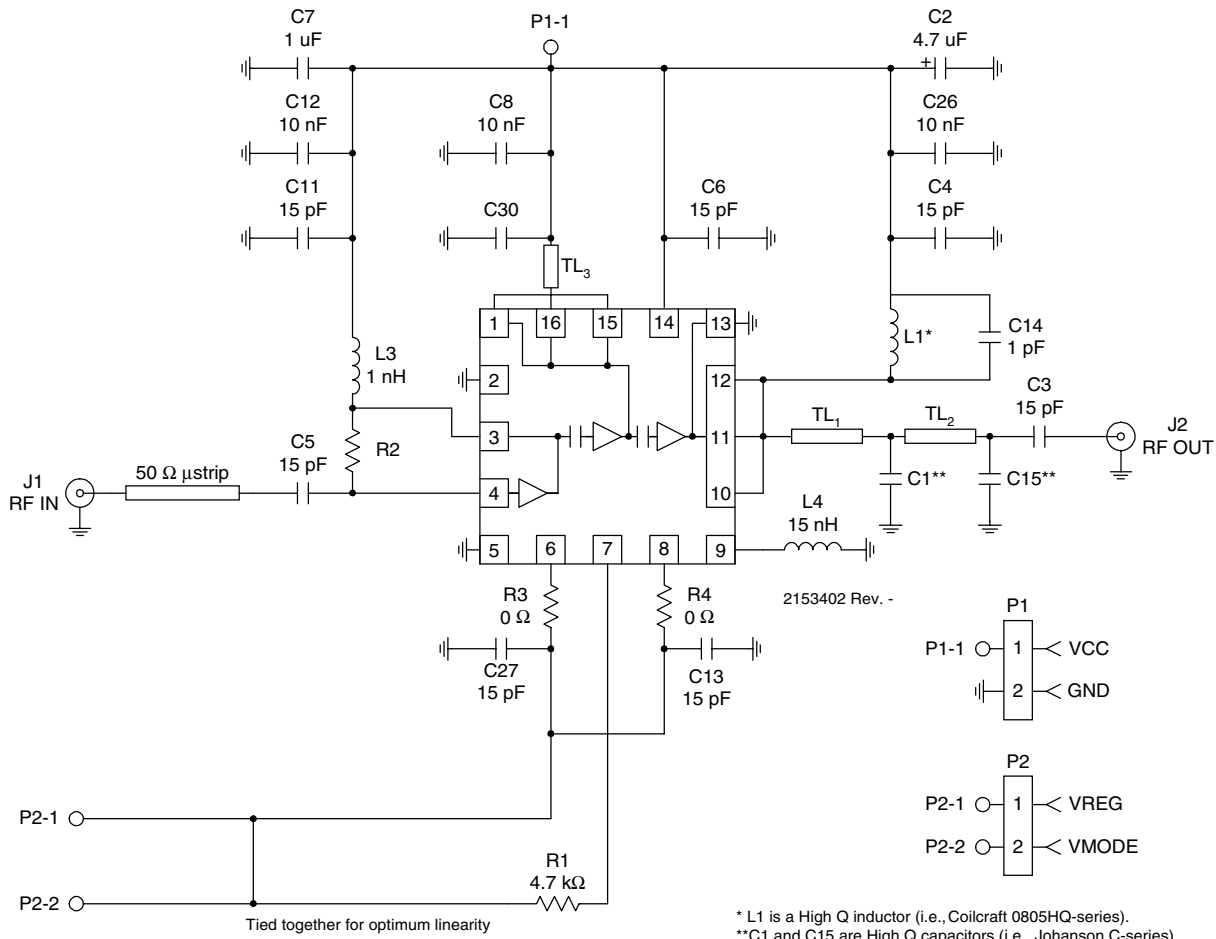
Evaluation Board Schematic Korea - CDMA



Board	R2 (Ω)	C30 (pF)	C1 (pF)	L1 (nH)	C15 (pF)
CDMA (Korea)	180	11	5.6	12	2.2

Transmission Line Length	TL ₁	TL ₂	TL ₃	TL ₄
CDMA (Korea)	30 mils	100 mils	30 mils	100 mils or ≥ 2.7 nH inductor

Evaluation Board Schematic
US - TDMA



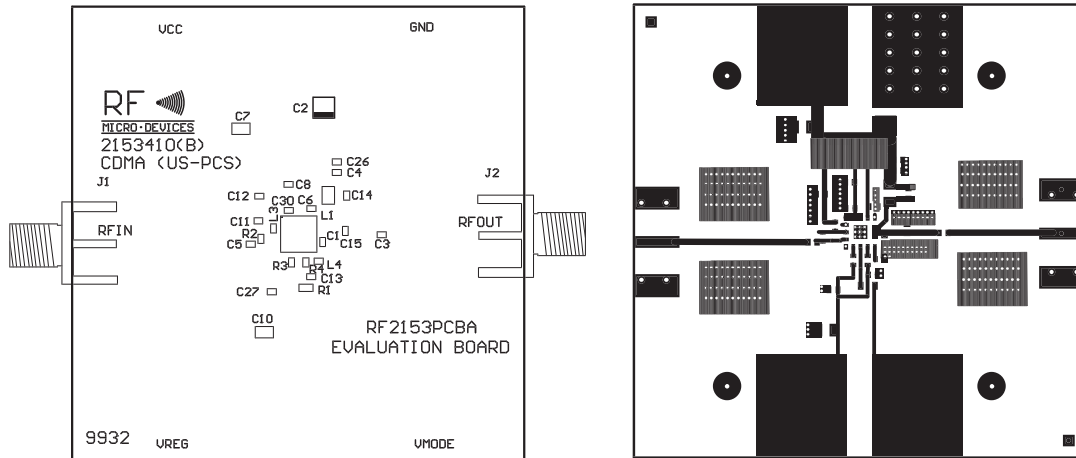
Board	R2 (Ω)	C30 (pF)	C1 (pF)	L1 (nH)	C15 (pF)
TDMA (US)	100	10	4.7	12	2.2

Transmission Line Length	TL ₁	TL ₂	TL ₃
TDMA (US)	20 mils	160 mils	10 mils

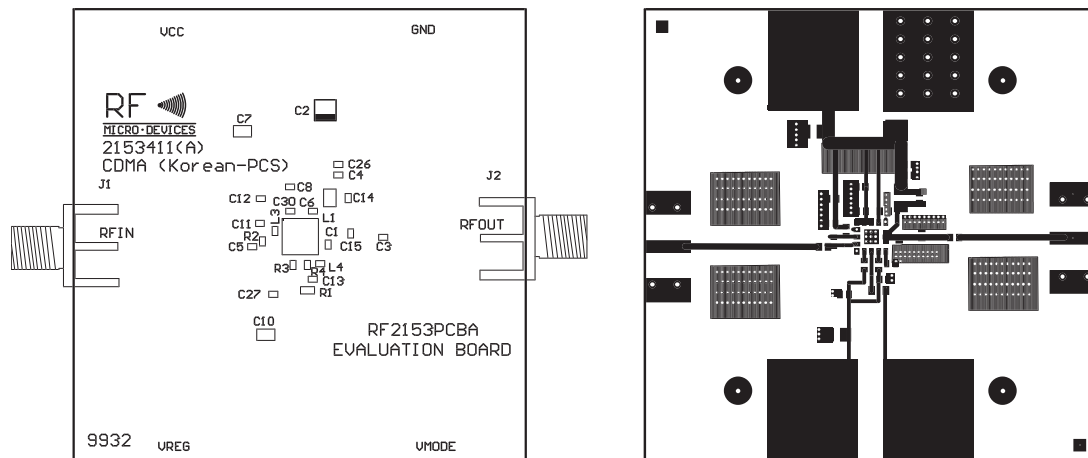
Evaluation Board Layout US - CDMA

Board Size 2.0" x 2.0"

Board Thickness 0.031", Board Material FR-4



Evaluation Board Layout Korea - CDMA



Evaluation Board Layout
US - TDMA

